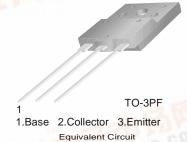


### FJAF6810D

# High Voltage Color Display Horizontal Deflection Output (Damper Diode Built-In)

- High Collector-Base Breakdown Voltage: BV<sub>CBO</sub> = 1500V
- High Switching Speed: t<sub>F</sub>(typ.) =0.1μs
- For Color TV



35Ω ty

# NPN Triple Diffused Planar Silicon Transistor

### Absolute Maximum Ratings T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Rating	Units V	
V <sub>CBO</sub>	Collector-Base Voltage	1500		
V <sub>CEO</sub>	Collector-Emitter Voltage	750	V	
V <sub>EBO</sub>	Emitter-Base Voltage	6	V	
I <sub>C</sub>	Collector Current (DC)	10	A	
	Collector Current (Pulse)	20	Α	
I <sub>CP</sub> * P <sub>C</sub>	Collector Dissipation	60	W	
T <sub>J</sub>	Junction Temperature	150	°C	
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C	

<sup>\*</sup> Pulse Test: Pulse Width=5ms, Duty Cycle ≤ 10%

### Electrical Characteristics T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
I <sub>CES</sub>	Collector Cut-off Current	V <sub>CB</sub> =1500V, R <sub>BE</sub> =0			1	mA
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> =800V, I <sub>E</sub> =0			10	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	V <sub>EB</sub> =4V, I <sub>C</sub> =0	40	In H	250	mA
BV <sub>EBO</sub>	Base-Emitter Breakdown Voltage	I <sub>E</sub> =300mA, I <sub>C</sub> =0	6	R	. 07	V
h <sub>FE1</sub> h <sub>FE2</sub>	DC Current Gain	V <sub>CE</sub> =5V, I <sub>C</sub> =1A V <sub>CE</sub> =5V, I <sub>C</sub> =6A	7 5	MAI.	8	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =6A, I <sub>B</sub> =1.5A			3	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> =6A, I <sub>B</sub> =1.5A			1.5	V
V <sub>F</sub>	Damper Diode Turn On Voltage	I <sub>F</sub> = 6A			2	V
t <sub>STG</sub> *	Storage Time	$V_{CC}$ =200V, $I_{C}$ =6A, $R_{L}$ =33 $\Omega$			3	μs
t <sub>F</sub> *	Fall Time	I <sub>B1</sub> =1.2A, I <sub>B2</sub> = - 2.4A			0.2	μs

<sup>\*</sup> Pulse Test: PW=20µs, duty Cycle=1% Pulsed

### Thermal Characteristics T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Тур	Max	Units
$R_{\theta jC}$	Thermal Resistance, Junction to Case		2.08	°C/W

## **Typical Characteristics**

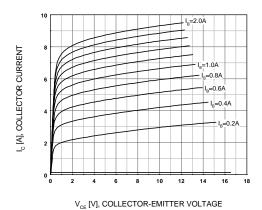


Figure 1. Static Characteristic

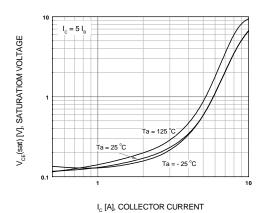


Figure 3. Collector-Emitter Saturation Voltage

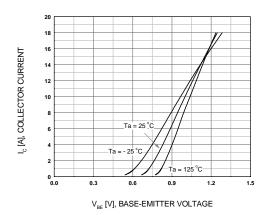


Figure 5. Base-Emitter On Voltage

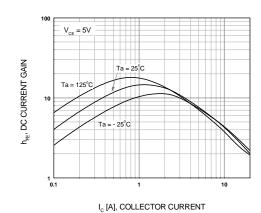


Figure 2. DC current Gain

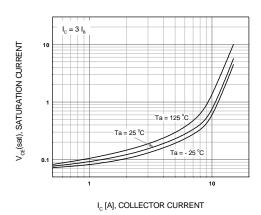


Figure 4. Collector-Emitter Saturation Voltage

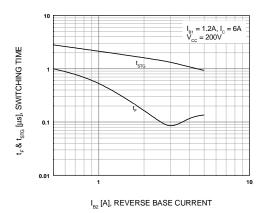


Figure 6. Resistive Load Switching Time

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## **Typical Characteristics** (Continued)

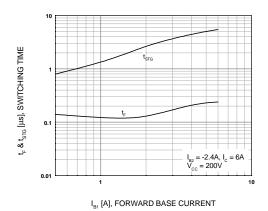


Figure 7. Resistive Load Switching Time

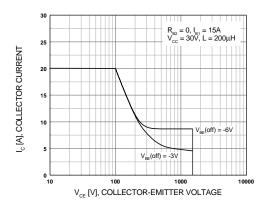


Figure 9. Reverse Bias Safe Operating Area

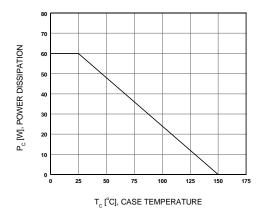


Figure 11. Power Derating

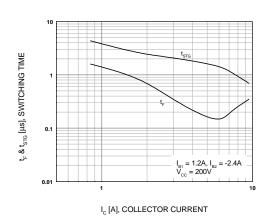


Figure 8. Resistive Load Switching Time

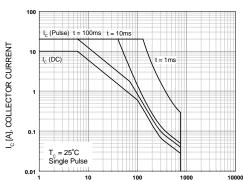
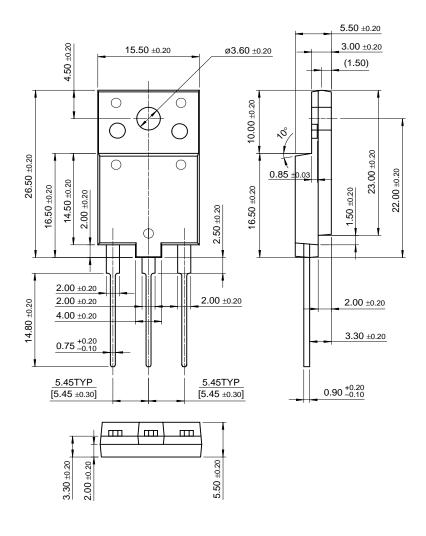


Figure 10. Forward Bias Safe Operating Area

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# **Package Demensions**

# TO-3PF



Dimensions in Millimeters

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DOME™	HiSeC™	PowerTrench <sup>®</sup>	SuperSOT™-8	
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